

# 3.3V, SOTiny<sup>TM</sup> 0.4 $\Omega$ Dual SPDT Analog Switch

#### **Features**

• CMOS Technology for Bus and Analog Applications

• Low On-Resistance: 0.4Ω (+2.7V Supply)

• Wide V<sub>DD</sub> Range: +1.5V to +4.2V

• Low Power Consumption : 5μW

· Rail-to-Rail switching throughout Signal Range

• Fast Switching Speed: 20ns max. at 3.3V

• High Off Isolation: -27dB at 100 kHz

 –41dB (100 kHz) Crosstalk Rejection Reduces Signal Distortion

• Extended Industrial Temperature Range: -40°C to 85°C

· Packaging:

- Pb-free & Green, 12-pin TDFN (ZE)

## **Applications**

- · Cell Phones
- PDAs
- · Portable Instrumentation
- Battery Powered Communications
- · Computer Peripherals

## **Pin Description**

Pin Number	Name	Description
8, 11	NOx	Data Port (Normally Open)
3, 6	GND	Ground
2, 5	NCx	Data Port (Normally Closed)
1, 4	COMx	Common Output/Data Port
9, 12	V <sub>DD</sub> x	Postive Power Supply <sup>(2)</sup>
7, 10	INx	Logic Control

#### **Notes:**

- 1. x = 0 or 1
- 2.  $V_{DD0}$  ad  $V_{DD1}$  are not internally connected. Each must be powered seperately.

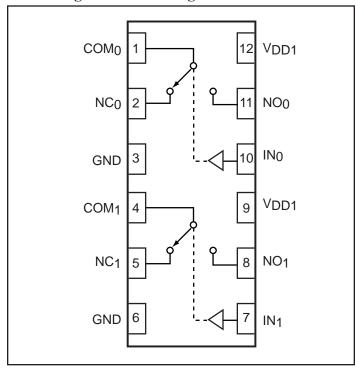
## **Description**

The PI3A3160 is a fast Dual single-pole double-throw (SPDT) CMOS switch. It can be used as an analog switch or as a low-delay bus switch. Specified over a wide operating power supply voltage range, +1.5V to +4.2V, the switch has an On-Resistance of  $0.4\Omega$  at 3.0V.

Control inputs, IN, tolerates input drive signals up to 3.3V, independent of supply voltage.

PI3A3160 is a lower voltage and On-Resistance replacement for the PI5A3158.

## **Block Diagram / Pin Configuration**



## **Function Table**

<b>Logic Input</b>	Function
0	NCx Connected to COMx
1	NOx Connected to COMx



# **Absolute Maximum Ratings**

Voltages Referenced to GND	
V <sub>DD</sub>	0.5V to +4.4V
V <sub>IN</sub> , V <sub>COM</sub> , V <sub>NC</sub> , V <sub>NO</sub> <sup>(1)</sup> or 30mA, whichever occurs first	$-0.5V$ to $V_+ + 0.3V$
Current (any terminal)	±200mA
Peak Current, COM, NO, NC (Pulsed at 1ms, 10% duty cycle)	±400mA

## **Thermal Information**

Continuous Power Dissipation	
SOT23 (derate 7.1mW/°C above +70°C)	W
Storage Temperature65°C to +150°	°C
Lead Temperature (soldering, 10s)+300	°C

Note 1: Signals on NC, NO, COM, or IN exceeding V<sub>DD</sub> or GND are clamped by internal diodes. Limit forward diode current to 30mA.

Caution: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied.

# **Electrical Specifications - Single +4.2V Supply**

 $(V_{DD} = +4.2V \pm 5\%, GND = 0V, V_{IH} = 1.6V, V_{IL} = 0.7V)$ 

Parameter	Symbol	Conditions	Temp. (°C)	Min.(1)	Typ. (2)	Max. (1)	Units	
Analog Switch								
Analog Signal Range (3)	V <sub>ANALOG</sub>		Full	0		$V_{\mathrm{DD}}$	V	
On Desigtance	D		25		0.4	0.45		
On Resistance	R <sub>ON</sub>	$V_{DD} = 4.0 V,$	Full			0.6		
On-Resistance Match	AD	$I_{COM} = 99 \text{mA},$ $V_{IN} = 0 \text{V to V}_{DD}$	25			0.08	Ω	
Between Channels <sup>(4)</sup>	$\Delta R_{\rm ON}$		Full			0.09		
On-Resistance Flatness <sup>(5)</sup>	R <sub>FLAT(ON)</sub>	$V_{DD} = 4.0V,$ $I_{COM} = 100 \text{mA}$	25			0.1		
On-Resistance Flatness			Full			0.1		
NO or NC Off Leakage	I <sub>NO(OFF)</sub> or	V <sub>DD</sub> =4.2V	25	-100		100		
Current <sup>(6)</sup>	I <sub>NC(OFF)</sub>	V <sub>DD</sub> =4.2 V	Full	-400		400	] <sub></sub>	
COM On Leakage Cur-	I <sub>COM(ON)</sub>	$V_{DD} = 4.2V$	25	-200		200	nA	
rent <sup>(6)</sup>			Full	-400		400		

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- 2. Typical values are for DESIGN AID ONLY, not guaranteed or subject to production testing.
- 3. Guaranteed by design.
- 4.  $\Delta R_{ON} = R_{ON} \text{ max.} R_{ON} \text{ min.}$
- 5. Flatness is defined as the difference between the maximum and minimum value of On-Resistance measured.
- 6. Leakage parameters are 100% tested at maximum rated hot temperature and guaranteed by correlation at +25°C.
- 7. Off Isolation =  $20\log_{10} [V_{COM} / (V_{NO} \text{ or } V_{NC})]$ . See Figure 4.
- 8. Between any two switches. See Figure 5.



# **Electrical Specifications - Single +3.3V Supply**

 $(V_{DD} = +3.3V \pm 10\%, GND = 0V, V_{IH} = 1.4V, V_{IL} = 0.5V)$ 

Parameter	Symbol	Conditions	Temp. (°C)	Min. <sup>(1)</sup>	Typ. (2)	Max. (1)	Units		
Analog Switch									
Analog Signal Range (3)	V <sub>ANALOG</sub>		Full	0		$V_{DD}$	V		
On Registance	D		25		0.4	0.45			
On Resistance	R <sub>ON</sub>	$V_{DD} = 2.7V$ ,	Full			0.6			
On-Resistance Match	A D	$I_{COM} = 100 \text{mA},$ $V_{NO} \text{ or } V_{NC} = +1.5 \text{V}$	25			0.08	Ω		
Between Channels <sup>(4)</sup>	$\Delta R_{\rm ON}$	THO ST VINC	Full			0.09			
(5)	R <sub>FLAT(ON)</sub>	$V_{DD} = 2.7V,$ $I_{COM} = 100 \text{mA},$ $V_{NO} \text{ or } V_{NC} = 0.8V, 2.0V$	25			0.1			
On-Resistance Flatness <sup>(5)</sup>			Full			0.1			
NO or NC Off Leakage	I <sub>NO(OFF)</sub> or	$V_{DD} = 3.3V$	25	-100		100			
Current <sup>(6)</sup>	I <sub>NC(OFF)</sub> of	$V_{COM} = 0V,$ $V_{NO} \text{ or } V_{NC} = +2.0V$	Full	-400		400			
COM On Leakage Current <sup>(6)</sup>	I <sub>COM(ON)</sub>	$V_{DD} = 3.3V$ ,	25	-200		200	nA		
		$V_{COM} = +2.0V,$ $V_{NO}$ or $V_{NC} = +2.0V$	Full	-400		400			

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- 4.  $\Delta R_{ON} = R_{ON} \text{ max.} R_{ON} \text{ min.}$
- 5. Flatness is defined as the difference between the maximum and minimum value of On-Resistance measured.
- Leakage parameters are 100% tested at maximum rated hot temperature and guaranteed by correlation at +25°C.
- 7. Off Isolation =  $20\log_{10} [V_{COM} / (V_{NO} \text{ or } V_{NC})]$ . See Figure 4.
- 8. Between any two switches. See Figure 5.



## **Electrical Specifications - Single +4.2V Supply**

 $(V_{DD} = +4.2V \pm 5\%, GND = 0V, V_{IH} = 1.6V, V_{IL} = 0.7V)$ 

Description	Param- eters	<b>Test Conditions</b>	Temp (°C)	Min. <sup>(1)</sup>	Typ.(2)	Max. <sup>(1)</sup>	Units
Logic Input							
Input High Voltage	V <sub>IH</sub>	Guaranteed logic High Level	Full	1.6			V
Input Low Voltage	$V_{\mathrm{IL}}$	Guaranteed logic Low Level				0.7	] v
Input Current with Voltage High	I <sub>INH</sub>	$V_{IN} = 1.4V$ , all others = $0.5V$		-1		1	
Input Current with Voltage Low	I <sub>INL</sub>	$V_{IN} = 0.5V$ , all other = 1.4V		-1		1	μA
Dynamic							
T. 0 T'	1.		25		Τ	20	
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 4.2V$ , $V_{NO}$ or	Full		İ	25	ns
T. OMT.		$V_{NC} = 2.0V$ , Figure 1	25			12	
Turn-Off Time			Full			15	
	t <sub>BBM</sub>	$V_{NO}$ or $V_{NC}$ = 1.5V, $R_L$ = 50 $\Omega$ , $C_L$ = 35pF, See Figure 8	25	1	12		
Break-Before-Make			Full	1			
Charge Injection <sup>(3)</sup>	Q	$C_L = 1$ nF, $V_{GEN} = 0$ V, $R_{GEN} = 0$ Ω, Figure 2	25		100		pC
Off Isolation <sup>(7)</sup>	O <sub>IRR</sub>	$R_L = 50\Omega$ , $f = 100$ kHz, Figure	3		-27		.tp
Cross Talk <sup>(8)</sup>	X <sub>TALK</sub>	$R_L = 50\Omega$ , $f = 100$ kHz, Figure	4		-41		dB
NC or NO Capacitance	C <sub>(OFF)</sub>	f = 1MHz, Figure 5			56		
COM Off Capacitance	C <sub>COM(OFF)</sub>	1 – TMHZ, Figure 3			56		pF
COM On Capacitance	C <sub>COM(ON)</sub>	f = 1MHz, Figure 6			160		
Supply							
Power-Supply Range	$V_{\mathrm{DD}}$		Full	1.5	Τ	3.6	V
Positve Supply Current	$I_{CC}$	$V_{DD} = 3.6V$ , $V_{IN} = 0V$ or $V_{DD}$	25			0.3	μА

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- 3. Guaranteed by design.
- 4.  $\Delta R_{ON} = R_{ON} \text{ max.} R_{ON} \text{ min.}$
- 5. Flatness is defined as the difference between the maximum and minimum value of On-Resistance measured.
- 6. Leakage parameters are 100% tested at maximum rated hot temperature and guaranteed by correlation at +25°C.
- 7. Off Isolation =  $20\log_{10} [V_{COM} / (V_{NO} \text{ or } V_{NC})]$ . See Figure 4.
- 8. Between any two switches. See Figure 5.



# **Electrical Specifications - Single +3.3V Supply**

 $(V_{DD} = +3.3V \pm 10\%, GND = 0V, V_{IH} = 1.4V, V_{IL} = 0.5V)$ 

Description	Param- eters	<b>Test Conditions</b>	Temp (°C)	Min. <sup>(1)</sup>	Typ.(2)	Max. <sup>(1)</sup>	Units
Logic Input							
Input High Voltage	V <sub>IH</sub>	Guaranteed logic High Level	Full	1.4			V
Input Low Voltage	$V_{\rm IL}$	Guaranteed logic Low Level				0.5	] V
Input Current with Voltage High	I <sub>INH</sub>	$V_{IN} = 1.4V$ , all others = $0.5V$		-1		1	
Input Current with Voltage Low	I <sub>INL</sub>	$V_{\rm IN}$ = 0.5V, all other = 1.4V		-1		1	μA
Dynamic							
T. 0 T'	1.		25			20	
Turn-On Time	$t_{ON}$	$V_{DD} = 3.3V$ , $V_{NO}$ or	Full			25	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{NC} = 2.0V$ , Figure 1	25			12	
Turn-OII Time			Full			15	
	t <sub>BBM</sub>	$V_{NO}$ or $V_{NC}$ = 1.5V, $R_L$ = 50 $\Omega$ , $C_L$ = 35pF, See Figure 8	25	1	12		
Break-Before-Make			Full	1			
Charge Injection <sup>(3)</sup>	Q	$C_L = 1$ nF, $V_{GEN} = 0$ V, $R_{GEN} = 0$ Ω, Figure 2	25		100		рC
Off Isolation <sup>(7)</sup>	O <sub>IRR</sub>	$R_L = 50\Omega$ , $f = 100$ kHz, Figure	3		-27		1D
Cross Talk <sup>(8)</sup>	X <sub>TALK</sub>	$R_L = 50\Omega$ , $f = 100$ kHz, Figure	4		-41		dB
NC or NO Capacitance	C <sub>(OFF)</sub>	f = 1MHz Eiguro 5			56		
COM Off Capacitance	C <sub>COM(OFF)</sub>	f = 1MHz, Figure 5			56		pF
COM On Capacitance	C <sub>COM(ON)</sub>	f = 1MHz, Figure 6			160		
Supply							
Power-Supply Range	$V_{\mathrm{DD}}$		Full	1.5		3.6	V
Positve Supply Current	I <sub>CC</sub>	$V_{DD} = 3.6V$ , $V_{IN} = 0V$ or $V_{DD}$	25			0.3	μА

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- 3. Guaranteed by design.
- 4.  $\Delta R_{ON} = R_{ON} \text{ max.} R_{ON} \text{ min.}$
- 5. Flatness is defined as the difference between the maximum and minimum value of On-Resistance measured.
- 6. Leakage parameters are 100% tested at maximum rated hot temperature and guaranteed by correlation at +25°C.
- 7. Off Isolation =  $20\log_{10} [V_{COM} / (V_{NO} \text{ or } V_{NC})]$ . See Figure 4.
- 8. Between any two switches. See Figure 5.



# **Electrical Specifications - Single +2.5V Supply**

 $(V_{DD} = +2.5V \pm 10\%, GND = 0V, V_{IH} = 1.4V, V_{IL} = 0.5V)$ 

Description	Parameters	<b>Test Conditions</b>	Temp.(°C)	Min. <sup>(1)</sup>	Typ.(2)	Max. <sup>(1)</sup>	Units
Analog Switch							
Analog Signal Range <sup>(3)</sup>	V <sub>ANALOG</sub>			0		$V_{\mathrm{DD}}$	V
On Resistance	R <sub>ON</sub>		25			0.5	
On Resistance	KON	$V_{DD} = 2.5V, I_{COM} = 80mA,$	Full			0.55	
On-Resistance Match	$\Delta R_{ m ON}$	$V_{NO}$ or $V_{NC} = 1.8V$	25			0.09	Ω
Between Channels (4)	AKON		Full			0.09	] \$2
On-Resistance Flatness <sup>(5)</sup>	D	$V_{DD} = 2.5V, I_{COM} = 80mA,$	25			0.1	
On-Resistance Flatness	R <sub>FLAT(ON)</sub>	$V_{NO} \text{ or } V_{NC} = 0.8V \ 1.8V$	Full			0.1	
Dynamic							
Turn-On Time	ton		25			20	-
Turn-On Time		$V_{DD} = 2.5V$ , $V_{NO}$ or $V_{NC} =$	Full			30	
T. 0 (%T)		1.8V, Figure 1	25			12	
Turn-Off Time	t <sub>OFF</sub>		Full			15	ns
Break-Before-Make	$t_{ m BBM}$	$V_{NO}$ or $V_{NC}$ = 1.5V, $R_L$ = 50 $\Omega$ , $C_L$ = 35pF, See Figure 8	25	1	15		
Charge Injection <sup>(3)</sup>	Q	$C_L = 1$ nF, $V_{GEN} = 0$ V, $R_{GEN} = 0$ V, Figure 2	25		60		pC
Logic Input							
Input HIGH Voltage	$V_{\mathrm{IH}}$	Guaranteed logic high level	Full	1.4			V
Input LOW Voltage	$V_{\rm IL}$	Guaranteed logic Low level	Full			0.5	
Input HIGH Current	I <sub>INH</sub>	$V_{IN} = 1.4V$ , all others = $0.5V$	Full	-1		1	A
Input HIGH Current	$I_{\mathrm{INL}}$	$V_{IN} = 0.5V$ , all others = 1.4V	Full	-1		1	μA

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- 3. Guaranteed by design.
- 4.  $\Delta R_{ON} = R_{ON} \text{ max.} R_{ON} \text{ min.}$
- 5. Flatness is defined as the difference between the maximum and minimum value of On-Resistance measured.



# **Electrical Specifications - Single +1.8V Supply**

 $(V_{DD} = +1.8V \pm 10\%, GND = 0V, V_{INH} = 1.4V, V_{INL} = 0.5V)$ 

Description	Parameters Parameters	<b>Test Conditions</b>	Temp.(°C)	Min. <sup>(1)</sup>	Typ.(2)	Max. <sup>(1)</sup>	Units
Analog Switch							
Analog Signal Range <sup>(3)</sup>	V <sub>ANALOG</sub>			0		$V_{\mathrm{DD}}$	V
On-Resistance	R <sub>ON</sub>		25			0.55	
On-Resistance	KON	$V_{DD} = 1.8V, I_{COM} = 60mA,$	Full			0.7	]
On-Resistance Match	$\Delta R_{ m ON}$	$V_{NO}$ or $V_{NC} = 1.5V$	25			0.03	$\Omega$
Between Channels (4)	ZIKON		Full			0.03	
On-Resistance Flat-	Pri ATKOND	$V_{DD} = 1.8V, I_{COM} = 60mA,$	25			0.9	
ness <sup>(5)</sup>	R <sub>FLAT(ON)</sub>	$V_{NO}$ or $V_{NC} = 0.8V$ , 1.5V	Full			1.1	
Dynamic							
Town On Time	4		25			40	
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 1.8V$ , $V_{NO}$ or $V_{NC} = 1.5V$ ,	Full			50	
Turn-Off Time	t <sub>OFF</sub>	Figure 1	25			12	]
Turn-OII Time			Full			15	ns
Break-Before-Make	t <sub>BBM</sub>	$V_{NO}$ or $V_{NC}$ = 1.5V, $R_L$ = 50 $\Omega$ , $C_L$ = 35pF, See Figure 8	25	1	30		
Charge Injection <sup>(3)</sup>	Q	$C_L = 1$ nF, $V_{GEN} = 0$ V, $R_{GEN} = 0$ V, Figure 2	25		40		рC
<b>Logic Input</b>							
Input HIGH Voltage	V <sub>IH</sub>	Guaranteed logic high level	Full	1.4			17
Input LOW Voltage	V <sub>IL</sub>	Guaranteed logic Low level	Full			0.5	V
Input HIGH Current	I <sub>INH</sub>	$V_{IN} = 1.4V$ , all others = 0.5V	Full	-1		1	
Input HIGH Current	I <sub>INL</sub>	$V_{IN} = 0.5V$ , all others =1.4V	Full	-1		1	μΑ

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- 5. Flatness is defined as the difference between the maximum and minimum value of On-Resistance measured.



## **Test Circuits/Timing Diagrams**

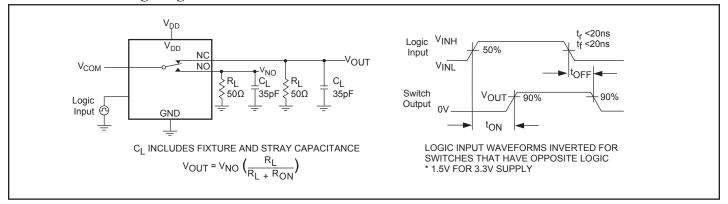


Figure 1. Switching Time

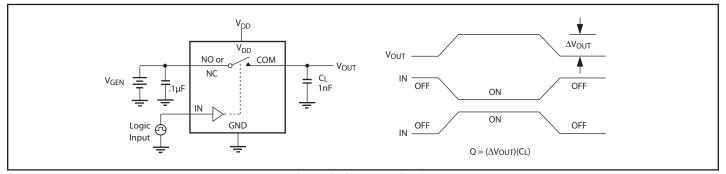


Figure 2. Charge Injection

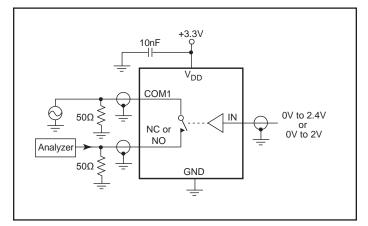


Figure 3. Off Isolation

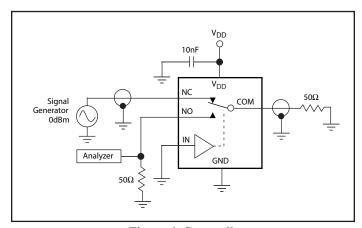


Figure 4. Crosstalk



## Test Circuits/Timing Diagrams (continued)

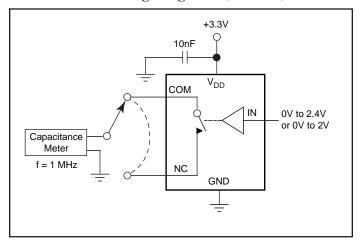


Figure 5. Channel-Off Capacitance

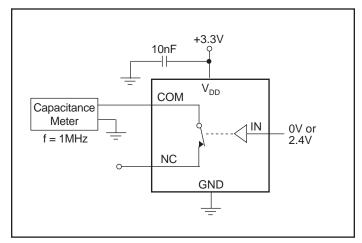


Figure 6. Channel-On Capacitance

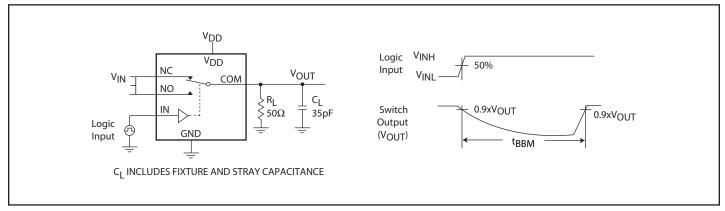
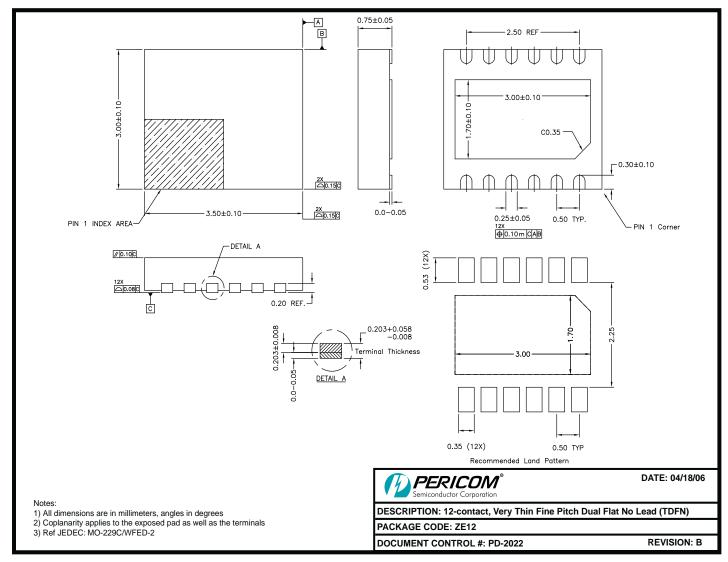


Figure 8. Break Before Make Diagram



# Packaging Mechanical: 12-Contact TDFN (ZE)



06-0360

#### Note:

• For latest package info, please check: http://www.pericom.com/products/packaging/mechanicals.php

## **Ordering Information**

	Ordering Code Package Code		Package Description	Top Mark	
F	PI3A3160ZEEX	ZE	Pb-free & Green, 12-contact TDFN	YI	

#### **Notes:**

- 1. Thermal characteristics can be found on the company web site at www.pericom.com/packaging/
- 2. X = Tape/Reel
- 3. Number of transistors = TBD

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